

isc Silicon NPN Power Transistor

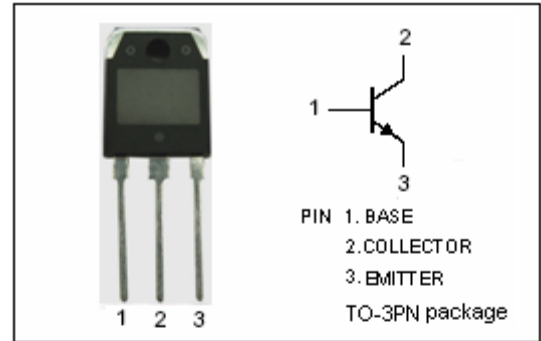
2SD1840

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 100V(\text{Min})$
- High Current Capability
- Wide Area of Safe Operation
- Complement to Type 2SB1230

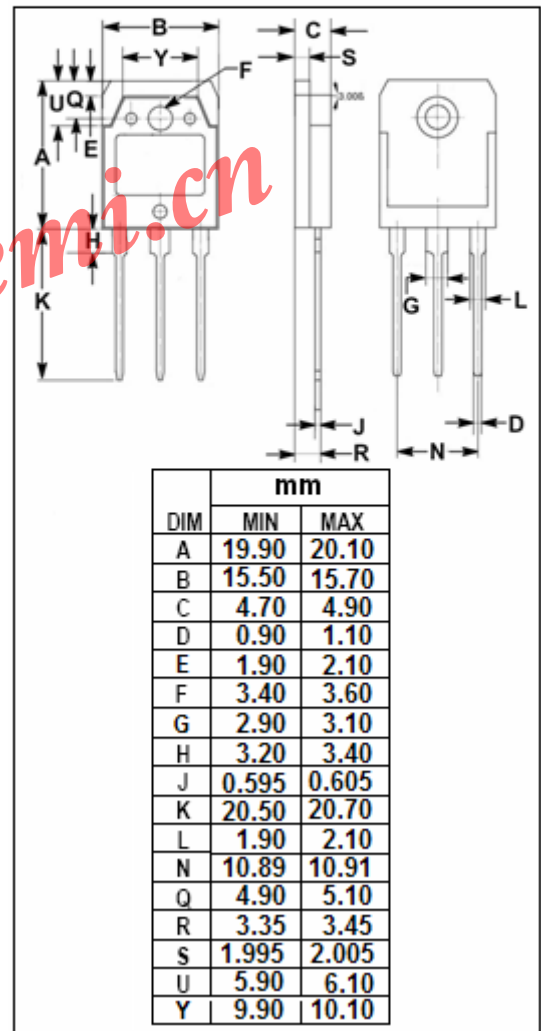
APPLICATIONS

- Designed for motor drivers, converters and other general high-current switching applications.



ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	110	V
V_{CEO}	Collector-Emitter Voltage	100	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	15	A
I_{CP}	Collector Current-Pulse	25	A
I_B	Base Current-Continuous	5	A
P_C	Collector Power Dissipation @ $T_a=25^{\circ}C$	3	W
	Collector Power Dissipation @ $T_C=25^{\circ}C$	100	
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



isc Silicon NPN Power Transistor**2SD1840****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=5\text{mA}; R_{BE}=\infty$	100			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C=1\text{mA}; I_E=0$	110			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=1\text{mA}; I_C=0$	6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=6\text{A}; I_B=0.6\text{A}$			0.8	V
$V_{BE(sat)}$	Base -Emitter Saturation Voltage	$I_C=6\text{A}; I_B=0.6\text{A}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=100\text{V}; I_E=0$			100	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			100	μA
h_{FE-1}	DC Current Gain	$I_C=1.5\text{A}; V_{CE}=2\text{V}$	50		140	
h_{FE-2}	DC Current Gain	$I_C=6\text{A}; V_{CE}=2\text{V}$	20			

◆ **h_{FE-1} Classifications**

P	Q
50-100	70-140